



Multimedia Available: Applied Materials' New DPN System Clears the Path to 65nm Transistor Gates

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Applied Materials Inc. extends transistor gate stack technology to the 65nm design node with its 300mm DPN Centura(R) system. The DPN(a) system delivers a robust integrated plasma nitridation and anneal process sequence that, for logic devices, allows equivalent oxide thickness (EOT) scaling to less than 11A (angstroms) and reduces gate leakage by 10x over thermal nitridation techniques.

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(a) DPN -- Decoupled Plasma Nitridation

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